Q.22 Describe Transistor as an amplifier in CE configuration.

SECTION-D

Note: Long answer type questions. Attempt any two questions out of three questions. (2x8=16)

Q.23 Explain any one D/A converter with Suitable Diagram.

Q.24 Discuss Construction, operation and characteristics of MOSFET.

Q.25 Describe Shift Resisters and their applications with suitable Diagram.

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2nd Sem. / Instrumentation and Control Engg., Medical Electronics
Subject : Analogue and Digital Electronics

Time : 3 Hrs. M.M. : 60

SECTION-A

Note: Multiple choice questions. All questions are compulsory (6x1=6)

Q.1 Donor type semiconductors are formed by adding impurity of valances_____.

a) 3 b) 5
c) 4 d) 6

Q.2 The circuit arrangement of a Transistor used as a buffer is_____.

a) CE b) CB
c) CC d) Both A and B

Q.3 FET can be used as_____.

a) Single stage Voltage amplifier.

b) Multi stage Voltage amplifier

c) Power Amplifier

d) All of these

Q.4 The base value of Octal No. System is_____

a) 2 b) 4

c) 8 d) 10

Q.5 A byte represents _____.

a) 3 nibble b) 8 nibble

c) 2 nibble d) 4 nibble

Q.6 D Flip Flop is_____Flip Flop.

a) Delayed b) Digital

c) Differential d) Dial type

SECTION-B

Note: Objective/ Completion type questions. All questions are compulsory. (6x1=6)

Q.7 Expand PIPO.

Q.8 Draw Symbol of OR Gate.

Q.9 Expand MOSFET.

Q.10 A transistor contains _____PN junction.

Q.11 Define Ripple.

Q.12 Mention name of any one A/D convertor.

SECTION-C

Note: Short answer type questions. Attempt any eight questions out of ten questions. (8x4=32)

Q.13 Write a short note on PN junction Diode.

Q.14 Discuss Structure of PNP Transistor.

Q.15 Explain NOT and AND Gate with their symbol and truth table.

Q.16 Write a short note on combinational Circuits.

Q.17 Differentiate between Analog and digital signals.

Q.18 Discuss I/P and O/P connections of CB configuration.

Q.19 Explain Diode as a Half wave rectifier.

Q.20 Describe characteristics and applications of Zener Diode.

Q.21 Differentiate between JFET and BJT.